
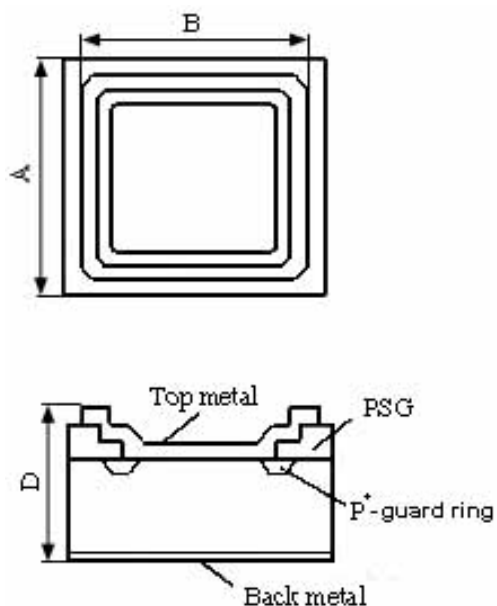


SCHOTTKY DIODES KDS 2130V.



Rev.1. Feb. 2010

 VSP-MIKRON	3A/40V. Die Size-65mil.			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10\text{mA}$	V_{BR}	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	3,0	-
DC Forward Voltage @ 25°C , $I_F=3,0\text{A}$	V_F	V	0,40	0,38 (0,37-typ)
Maximum Reverse Current @ 25°C , $V_R=40\text{V}$ 25°C , $V_R=45\text{V}$ 100°C , $V_R=40\text{V}$	I_R	mA	0,6 - 50,0	0,5 0,7 45,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	110	-
Peak Repetitive Reverse Surge Current @ $2,0\mu\text{s}$, $f=1\text{kHz}$., $T_J<125^\circ\text{C}$.	I_{RRM}	A	2,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	± 8 (contact)	
Voltage Rate of Change	dV/dt	V/ μS	10.000	
Operating Junction Temperature	T_J	$^\circ\text{C}$	125	



DIM	ITEM	μm
A_x A_y	Wafer Form Die Size	1650 1650
B_x B_y	Top Metal Size	1470 1470
D	Thickness	300max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;
b) **Al-Ni-Ag** – for Soldering.
Backside metal: **Ti-Ni-Ag**.